

#### BSS100 / BSS123

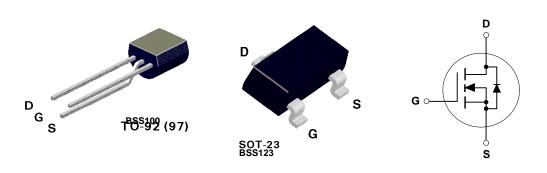
# N-Channel Logic Level Enhancement Mode Field Effect Transistor

#### **General Description**

These N-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance. This product is particularly suited to low voltage, low current applications, such as small servo motor controls, power MOSFET gate drivers, and other switching applications.

#### **Features**

- BSS100: 0.22A, 100V.  $R_{DS(ON)} = 6\Omega$  @  $V_{GS} = 10V$ . BSS123: 0.17A, 100V.  $R_{DS(ON)} = 6\Omega$  @  $V_{GS} = 10V$
- High density cell design for extremely low R<sub>DS(ON)</sub>.
- Voltage controlled small signal switch.
- Rugged and reliable.



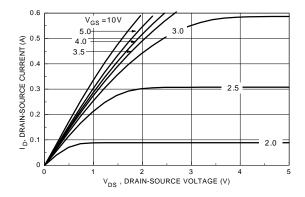
### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	BSS100	BSS123	Units
V <sub>DSS</sub>	Drain-Source Voltage	1	V	
$V_{DGR}$	Drain-Gate Voltage ( $R_{GS} \le 20K\Omega$ )	1	00	V
V <sub>GSS</sub>	Gate-Source Voltage - Continuous	±	: 14	V
	- Non Repetitive (T <sub>P</sub> < 50 μS)	±	:20	
I <sub>D</sub>	Drain Current - Continuous	0.22	0.17	А
	- Pulsed	0.9	0.68	
$P_{D}$	Total Power Dissipation @ T <sub>A</sub> = 25°C	0.63	0.36	W
$T_J$ , $T_{STG}$	Operating and Storage Temperature Range	-55	℃	
T <sub>L</sub>	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	3	.€	
THERMA	L CHARACTERISTICS			
$R_{\theta JA}$	Thermal Resistacne, Junction-to-Ambient	200	350	°C/W

Symbol	Parameter	Type	Min	Тур	Max	Units	
OFF CHA	RACTERISTICS				ı		.1
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	All	100			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	BSS100			15	μΑ
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	BSS123			1	μA
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$ $T_{J} = 125^{\circ}\text{C}$	All			60	μΑ
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	BSS100			10	nA
		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	BSS123			10	nA
I <sub>GSSF</sub>	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	BSS100			10	nA
		$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	BSS123			50	nA
ON CHAR	ACTERISTICS (Note 1)	·	•				•
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 1 \text{ mA}$	All	0.8	1.4	2	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 0.22 \text{ A}$	BSS100		2.8	6	Ω
. ,		$V_{GS} = 10 \text{ V}, I_{D} = 0.17 \text{ A}$	BSS123		2.8	6	
		$V_{GS} = 4.5 \text{ V}, I_{D} = 0.22 \text{ A}$	BSS100		3.2	10	1
		$V_{GS} = 4.5 \text{ V}, I_{D} = 0.17 \text{ A}$	BSS123		3.2	10	
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 0.22 \text{ A}$	BSS100	80.0	0.4		S
		$V_{DS} = 10 \text{ V}, I_{D} = 0.17 \text{ A}$	BSS123	0.08	0.4		
DYNAMIC	CHARACTERISTICS	·	•				•
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, \ V_{GS} = 0 \text{ V}, $ $f = 1.0 \text{ MHz}$	All		29	60	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz	All		10	15	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		All		2	6	pF
SWITCHIN	IG CHARACTERISTICS (Note 1)		•		3	•	-
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, \ I_{D} = 0.28 \text{ A},$	All			8	ns
t <sub>r</sub>	Turn - On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 50 \Omega$	All			8	ns
$\mathbf{t}_{D(off)}$	Turn - Off Delay Time		All			13	ns
t <sub>f</sub>	Turn - Off Fall Time		All			16	ns
$Q_g$	Totall Gate Charge	$V_{DS} = 10 \text{ V}, I_{D} = 0.22 \text{ A},$	All		1.4	2	nC
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 10 \text{ V},$	All		0.15	0.25	nC
$Q_{gd}$	Gate-Drain Charge		All		0.2	0.4	nC
DRAIN-SO	DURCE DIODE CHARACTERISTICS AND I	MAXIMUM RATINGS					
Is	Maximum Continuous Source Current	BSS100			0.22	Α	
			BSS123			0.17	
$I_{\rm SM}$	Maximum Pulse Source Current (Note 1)		BSS100			0.9	Α
			BSS123			0.68	
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \ I_{S} = 0.44 \text{ A}$	BSS100		0.9	1.3	V
		$V_{GS} = 0 \text{ V}, I_{S} = 0.34 \text{ A}$	BSS123		0.9	1.3	

Note: 1. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

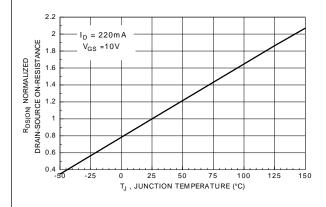
## **Typical Electrical Characteristics**



2.4 V<sub>GS</sub> = 2.5V V<sub>GS</sub> = 2.5V V<sub>GS</sub> = 2.5V 3.0 3.5 3.5 3.5 1.0 0.1 0.2 0.3 0.4 0.5 0.6 1.0 0.5 0.6

Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.



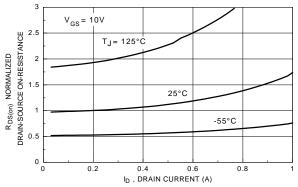
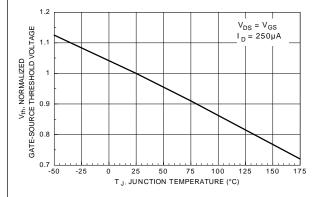


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Drain Current and Temperature.



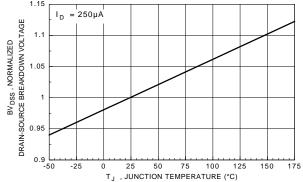


Figure 5. Gate Threshold Variation with Temperature.

Figure 6. Breakdown Voltage Variation with Temperature.

### **Typical Electrical Characteristics (continued)**

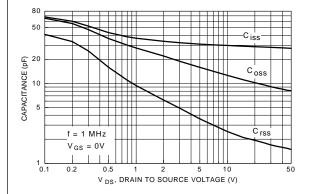


Figure 7. Capacitance Characteristics.

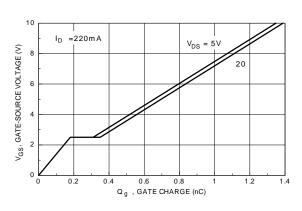


Figure 8. Gate Charge Characteristics.

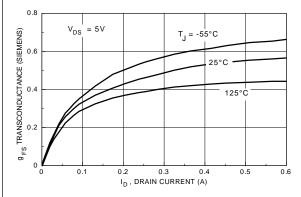


Figure 9. Transconductance Variation with Drain Current and Temperature.

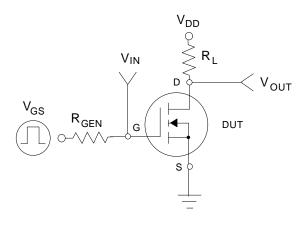


Figure 10. Switching Test Circuit.

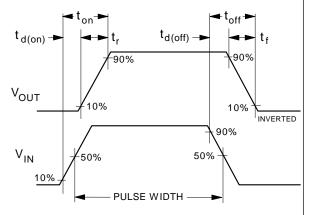
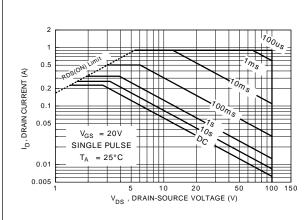


Figure 11. Switching Waveforms.



0.5 0.5 0.5 0.05 0.05 0.0

Figure 12. BSS100 Maximum Safe Operating Area.

Figure 13. BSS123 Maximum Safe Operating Area.

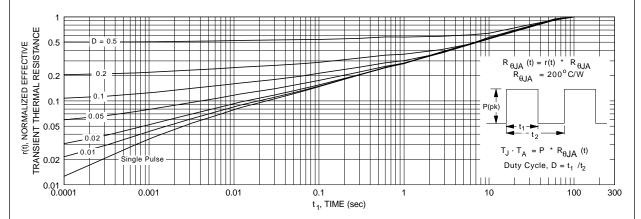


Figure 14. BSS100 Transient Thermal Response Curve.

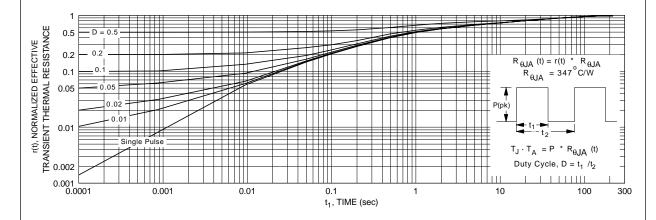
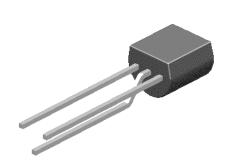


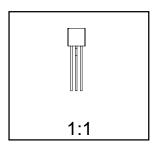
Figure 15. BSS123 Transient Thermal Response Curve.

# **TO-92 Package Dimensions**



# TO-92; TO-18 Reverse Lead Form (J35Z Option) (FS PKG Code 92, 94, 96)

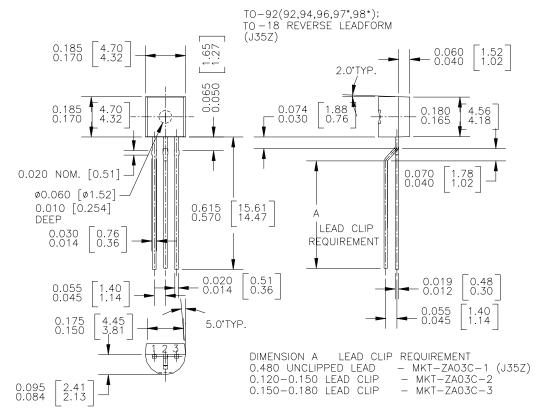




Scale 1:1 on letter size paper

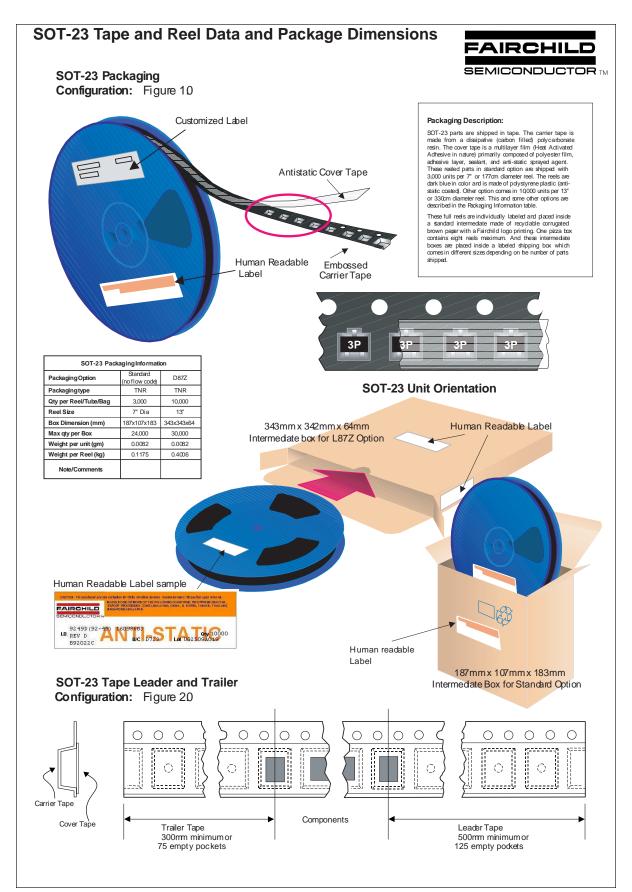
Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.22



**Note:** All package 97 or 98 transistors are leadformed to this configuration prior to bulk shipment. Order L34Z option if in-line leads are preferred on package 97 or 98.

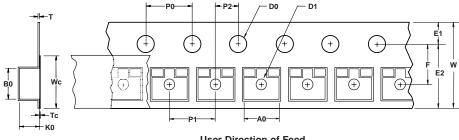
<sup>\*</sup> Standard Option on 97 & 98 package code



# SOT-23 Tape and Reel Data and Package Dimensions, continued

# **SOT-23 Embossed Carrier Tape**

Configuration: Figure 3.0



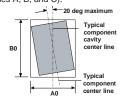
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



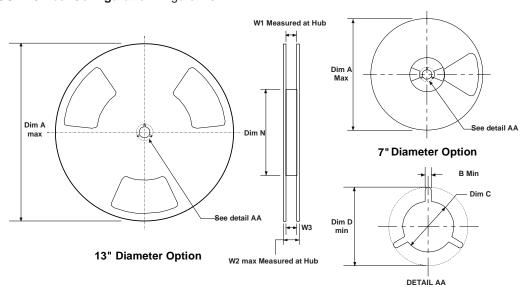
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

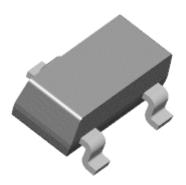
#### SOT-23 Reel Configuration: Figure 4.0

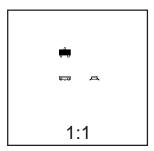


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

# SOT-23 Tape and Reel Data and Package Dimensions, continued

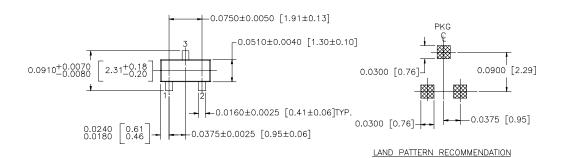
# SOT-23 (FS PKG Code 49)

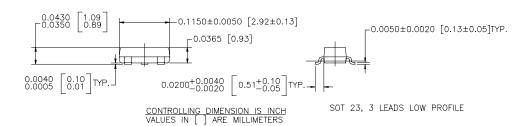




Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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Datasheet Identification	Product Status	Definition					
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